Ordering number: ENN6091

TR: NPN Silicon Epitaxial Planar Transistor
SBD: Schottky Barrier Diode

CPH5702



DC/DC Converter Applications

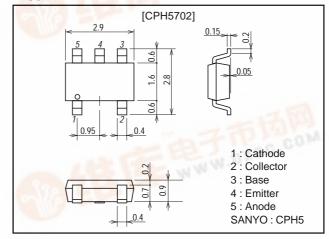
Features

- Composite type with a NPN transistor and a Schottky barrier diode contained in one package facilitating high-density mounting.
- The CPH5702 consists of two chips encapsulated in a package which are equivalent to the CPH3209 and the SB07-03C, respectively.
- · Ultrasmall-sized package permitting applied sets to be made small and slim (0.9mm).

Package Dimensions

unit:mm

2156



Specifications

Absolute Maximum Ratings at Ta = 25°C

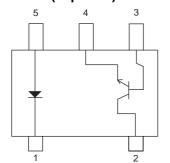
Parameter	Symbol	Conditions	Ratings	Unit
[TR]				
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO	140	30	V
Emitter-to-Base Voltage	V _{EBO}		5	V
Collector Current	IC	- 1.20 Table 1	3	Α
Collector Current (Pulse)	ICP	AND ASSESSMENT OF THE PARTY OF	5	Α
Base Current	IB	NO.	600	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm²×0.8mm)	0.9	W
Junction Temperature	Tj	D Last	150	°C
Storage Temperature	Tstg	- CO	-55 to +125	°C
[SBD]	M.D.		·	
Repetitive Peak Reverse Voltage	V _{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V _{RSM}		35	V
Average Output Current	Io		700	mA
Surge Current	I _{FSM}	50Hz sine wave, 1 cycle	5	Α
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg	- 12 To 12 T	-55 to +125	°C

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Electrical Characteristics at Ta = 25°C

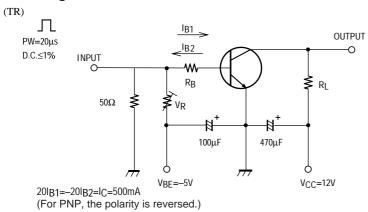
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Offic
[TR]	•					
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0			0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μΑ
DC Current Gain	hFE	V _{CE} =2V, I _C =500mA	200		560	
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =500mA		450		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		20		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)} 1	I _C =1.5A, I _B =30mA		120	185	mV
	V _{CE(sat)} ²	I _C =1.5A, I _B =75mA		105	155	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1.5A, I _B =30mA		0.83	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0	40			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =1mA, R _{BE} =∞	30			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5			V
Turn-ON Time	ton	See specified Test Circuit.		30		ns
Storage Time	t _{stg}	See specified Test Circuit.		300		ns
Turn-OFF Time	t _f	See specified Test Circuit.		15		ns
[SBD]	·					
Reverse Voltage	V _R	I _R =300μA	30			V
Forward Voltage	٧F	I _F =700mA			0.55	V
Reverse Current	I _R	V _R =15V			80	μΑ
Interterminal Capacitance	С	V _R =10V, f=1MHz cycle		28		pF
Reverse Recovery Time	t _{rr}	I _F =I _R =100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rthj-a	Mounted on a ceramic board (600mm²×0.8mm)		151		°C/W

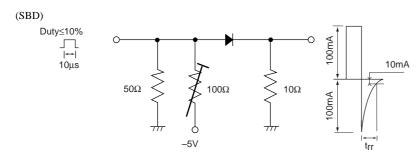
Electrical Connection (Top view)

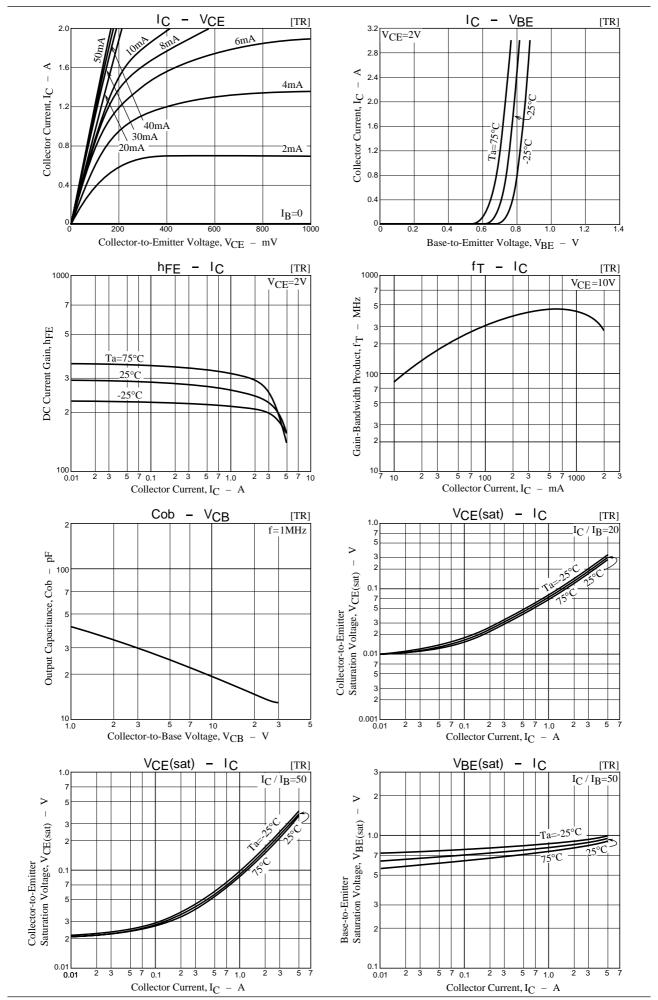


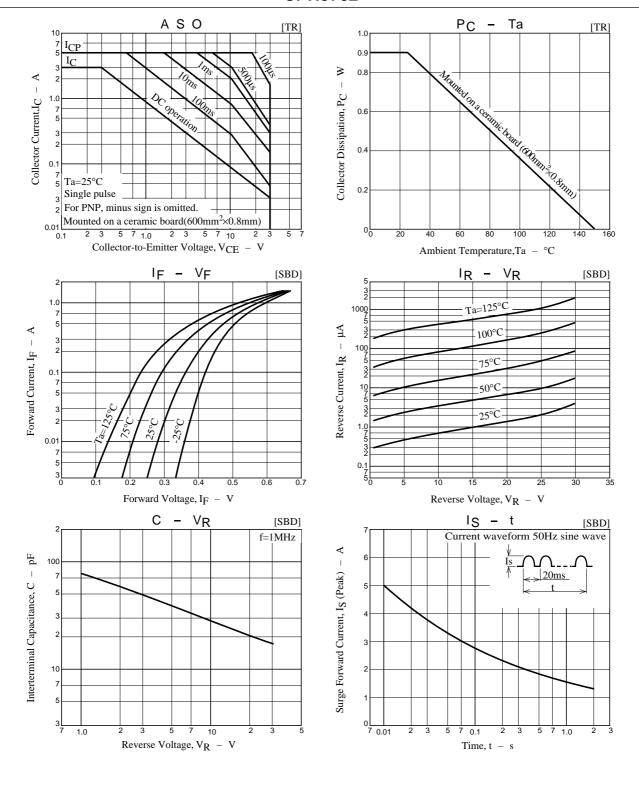
- 1 : Cathode
- 2 : Collector
- 3: Base
- 4 : Emitter
- 5 : Anode

Switching Time Test Circuit









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